

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	610649	(measur\$4 detect\$4 sens\$4 detect\$4 transducer) near3 (strain stress force load\$4 pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:24
L2	188	1 and ("indium antimonide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:24
L3	90	2 and (plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:24
L4	5	3 and (mesa)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:25
L5	1	4 and (filling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:24
L6	0	5 and (inhomogenous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:24
L7	84163	(measur\$4 detect\$4 sens\$4 detect\$4 transducer) near3 (strain stress force load\$4 pressure).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:47
L8	23	7 and ("indium antimonide")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:24
L9	11	8 and (plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:25

L10	0	9 and (inhomogenous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:37
L11	1	9 and (filling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:27
L12	1	9 and (mesa)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:27
L13	468	7 and (mesa)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:28
L14	3	13 and ("filling factor")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:28
L15	1966	1 and (mesa)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:29
L16	3	15 and ("filling factor")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:28
L17	3	15 and (filling near3 factor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:29
L18	2766	(filling near3 factor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:30
L19	21	18 and (interface) near3 (strain stress force load\$4 pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:36

L20	1	19 and (mesa)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:31
L21	8763	(fill\$4 near3 factor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:34
L22	118	21 and (interface) near3 (strain stress force load\$4 pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:31
L23	4	22 and (mesa)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:38
L24	64	22 and (semiconduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:40
L25	61	24 and (metal\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:32
L26	1	9 and (fill\$4 near3 factor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:37
L27	6	9 and (fill\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:35
L28	36116	(interface) near3 (strain stress force load\$4 pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:36
L29	118	28 and (fill\$4 near3 factor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:37

L30	0	29 and (inhomogenous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:37
L31	1	29 and (inhomogeneous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:37
L32	199	28 and (inhomogeneous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:46
L33	12	32 and (mesa)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:38
L34	84	32 and (semiconduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:40
L35	81	34 and (metal\$4 conduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:40
L36	6	(inhomogeneous) near3 (semiconduct\$4).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:46
L37	104	(inhomogeneous) near3 (semiconduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:50
L38	3	37 and (measur\$4 detect\$4 sens\$4 detect\$4 transducer) near3 (strain stress force load\$4 pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:48
L39	58	37 and (strain stress force load\$4 pressure)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:50

L40	982925	(strain stress force load\$4 pressure).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:50
L41	150	40 and (inhomogeneous) near3 (semiconduct\$4 layer sheet film pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:51
L42	12	40 and (inhomogeneous) near3 (semiconduct\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/09/14 10:51